

Application No. 10/042,342

A1

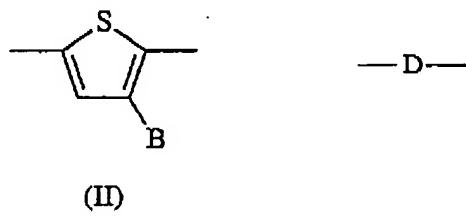
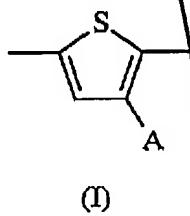
processes thereof and uses thereof illustrated in these copending applications may be selected for the present invention in embodiments thereof.

IN THE CLAIMS:

Please substitute the following amended Claims 6 and 17 for pending Claims 6 and 17:

*Sub B
B1*

6. (Amended) A thin film transistor device comprised of a substrate, a gate electrode, a gate dielectric layer, a source electrode and a drain electrode, and a semiconductor layer comprised a polythiophene derived from a monomer segment or monomer segments containing two 2,5-thienylene segments, (I) and (II), and an optional divalent linkage D

A2

—D—

wherein A is a side chain; B is hydrogen or a side chain; and D is a divalent linkage, and wherein the number of A-substituted thiophene units (I) in the monomer segments is from about 1 to about 10, the number of B-substituted thiophene units (II) is from 0 to about 5, and the number of divalent linkages D is 0 or 1.

A3

17. (Amended) A thin film transistor device in accordance with claim 6 wherein D is a divalent linkage optionally comprised of a saturated moiety of alkylene, -O-R-O-, -S-R-S-, -NH-R-NH-, where R is alkylene or arylene, or an unsaturated moiety of an arylene or heteroaromatics.

Please cancel Claims 1 to 5 without prejudice.